

1 Fabrication of polymer photonic crystal superprism structures using 2 polydimethylsiloxane soft molds

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7 We presented a soft lithography technique of fabricating polymer photonic crystal superprism
8 structures using elastomeric polydimethylsiloxane templates. Dense two-dimensional photonic
9 crystal superprism structures with feature sizes of 150–500 nm and aspect ratios of up to 1.25 were
10 replicated. Large field size and easy fabrication are two major advantages when compared with other
11 imprint technology. Atomic force microscopy images showed that the molded structures had high
12 fidelity to the masters. Less than 3% reduction of the depth in the molded structures was achieved
13 with respect to the master. The increase of the surface roughness from the master to the molded
14 structures is minimal. The issue of pattern collapse during pattern transfer of submicron structures
15 was analyzed against the pattern dimensions and aspect ratios; and the experimental results were
16 found in agreement with a prior theory. We also experimentally demonstrated the superprism effect
17 in two-dimensional photonic crystal structure at near-infrared wavelength. The propagation beam
18 changed 39° in the photonic crystal with respect to the input wavelength varying from
19 1546 to 1572 nm. Such an effective, low cost, and high throughput soft lithography technique could
20 find wide use in making photonic crystal based nanostructures. © 2007 American Institute of
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29 INTRODUCTION

24 Nanophotonics shows the promise to have a revolution-
25 ary impact on the landscape of photonics technology. Photo-
26 nic crystal based nanostructures are anticipated to play a sig-
27 nificant role in next generation photonic devices. Photonic
28 crystals are artificial dielectric periodic structures. They can
29 form functional photonic devices with significantly reduced
30 sizes and prominent characteristics, such as high wavelength
31 and angular sensitivity¹ and significant group velocity
32 dispersion.^{2,3} Recently, devices based on two-dimensional
33 (2D) photonic crystal slabs have stirred up widespread inter-
34 est as such 2D planar photonic structures are compatible with
35 conventional microelectronic and photonic devices. Myriads
36 of optical components such as waveguides, resonators, de-
37 multiplexers, and modulators have been designed and fabri-
38 cated based on 2D photonic crystal geometry.^{1–5}

39 Polymers, a class of materials that can be integrated with
40 virtually all other substrates, have been considered as a
41 promising material candidate for photonic crystals. Polymer
42 photonic crystal slabs usually do not exhibit complete pho-
43 tonic band gaps because of low dielectric constants of poly-
44 mers. However, certain optical devices such as superprism
45 based demultiplexers do not require the photonic crystals to
46 have a band gap.⁷

47 To fabricate polymeric photonic crystals, many efforts
48 have been focused on conventional processing techniques
49 such as electron-beam (e-beam) nanolithography and reac-
50 tive ion etching (RIE), which are relatively complicated,
51 costly, and time consuming. Imprint lithography is one of the
52 promising methods for making microstructures and nano-

53 structures owing to low cost and high throughput. Most
54 prominent among these methods are hot embossing, step and
55 flash imprint lithography (SFIL), and soft lithography.^{8–17}
56 Hot embossing lithography employs a silicon or nickel tem-
57 plate to imprint the resist above its glass transition tempera-
58 ture with large pressure applied. The heating cycle extends
59 the process time and pattern distortion can occur due to high
60 temperature and large pressure. The imprint area is limited
61 by the waviness of the substrate. SFIL can be used to imprint
62 high resolution patterns over a large area by step and repeat.
63 However, imprinting on a 100 mm wafer size can be realized
64 using polydimethylsiloxane (PDMS) template in one single
65 step.¹¹ Soft lithography utilizes elastomeric PDMS with re-
66 lief patterns to replicate micro- and nanostructures.⁹ A PDMS
67 template is generally prepared by casting prepolymer against
68 a master patterned by conventional lithography techniques.
69 One advantage of soft lithography that utilizes PDMS rather
70 than ridged template is that it can conform to a substrate over
71 large areas without external force. A second advantage of
72 PDMS is that it is easily removed from the master and
73 molded structures. For hot embossing and SFIL, it is neces-
74 sary to coat an antisticking layer on the template to com-
75 pletely release it from the imprinted polymer. Even though
76 the template surface is treated with a low surface energy
77 surfactant, the imprinted polymer tends to adhere to the tem-
78 plate and cause defects when imprinting dense or high aspect
79 ratio patterns.¹³

80 The line and hole structures at nanoscale with aspect
81 ratio considerably smaller than 1 were demonstrated using
82 soft lithography in recent years.^{10,14} However, it becomes
83 challenging to replicate structures with aspect ratios larger
84 than 1 and feature sizes smaller than 500 nm in part because

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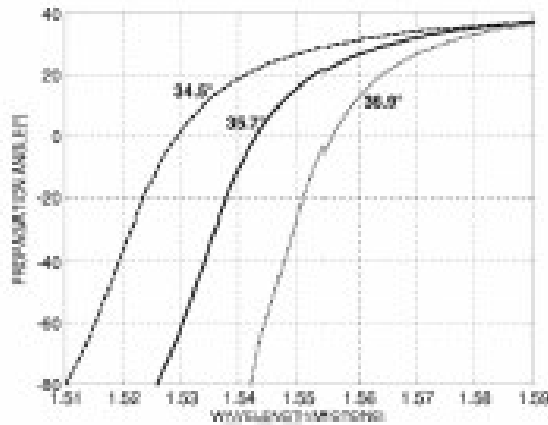


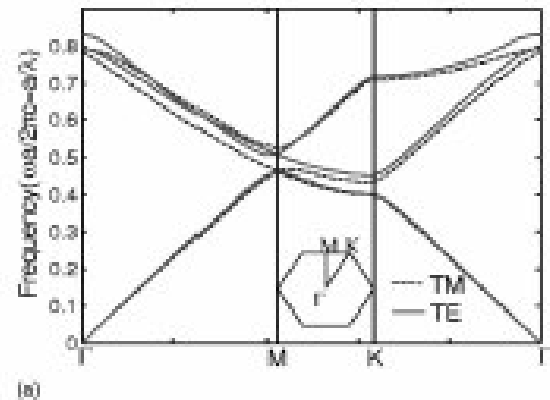
FIG. 2. (Color online) Propagation angle as a function of the normalized frequency for different incident angles.

85 of the low modulus of PDMS. These features are desired in
86 many soft lithography applications such as fabricating pho-
87 tonic crystals. When the feature size shrinks to submicro- or
88 nanoscale, the aspect ratio (depth/width) and pattern density
89 (width/spacing) play an important role in the PDMS defor-
90 mation. For high aspect ratio structures, lateral collapse can
91 easily occur owing to capillary and other forces during the
92 pattern transfer of submicron structures.²⁰ In this work, we
93 employed soft lithography to fabricate fine structures with
94 aspect ratios larger than 1 and feature sizes in the range of
95 100–500 nm. We also investigated the deformation of
96 PDMS in making dense photonic crystal patterns.

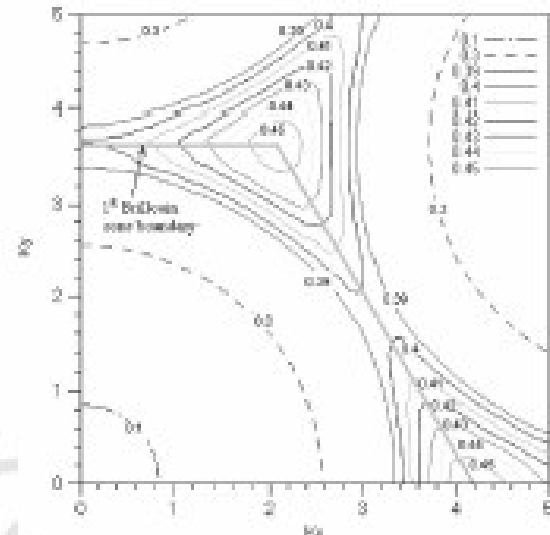
97 SIMULATION

98 Before the fabrication of the 2D polymer photonic crys-
99 tal, the photonic crystal superprism structure with a triangle
100 array of air holes was designed and calculated. The refractive
101 index of background polymer is 1.475 at 1550 nm. To opti-
102 mize the design of superprism for low index contrast photo-
103 nic crystals, the complete band structure and the dispersion
104 surface were calculated and analyzed by the plane wave
105 expansion.²¹ Figure 1(a) shows the calculated band structure
106 of a triangle lattice with a polymer refractive index of 1.475.
107 The hole radius is $r=0.25a$, where a is the lattice constant.
108 The inset shows the first Brillouin zone and its symmetry
109 points. There is no complete photonic band gap for trans-
110 verse electric (TE) mode (electric field parallel to the plane)
111 and transverse magnetic (TM) mode (magnetic field parallel
112 to the plane) due to low refractive index contrast.

113 The dispersion surface is determined by the band struc-
114 ture in various directions. For a given incident wave vector,
115 the propagation direction can be obtained through the mo-
116 mentum conservation rule and group velocity $v_g = \nabla_{\mathbf{k}} \omega(\mathbf{k})$
117 which is normal to the dispersion surface.¹ The dispersion
118 surface of the first band (TE mode) is shown in Fig. 1(b). At
119 low normalized frequency ($\omega a / 2\pi c < 0.4$), the band struc-
120 ture is isotropic and the dispersion surface is circlelike with a
121 radius given by the magnitude of wave vector. For the non-
122 normalized frequencies in the range of 0.4–0.45, the band struc-
123 ture is strongly anisotropic and the dispersion surface is dis-
124 torted from circle. The propagation direction is sensitive to



(a)



(b)

FIG. 1. (Color online) (a) Photonic band structure of a triangle array of air holes on the polymer with a polymer refractive index of 1.475. (b) Contour curve of dispersion surface of the first band (TE mode).

the wavelength of incident light and incident angle at the 125
sharp corner region of the dispersion surface. Figure 2 shows 126
the propagation angle in the photonic crystal as a function of 127
the wavelength for the different incident angles. The photo- 128
nic crystal structure is an array of air holes in the polymer 129
with 325 nm in diameter (lattice constant of 650 nm). For 130
the incident angle of 36.9°, the propagation angle changes 131
from -51° to 28° when the wavelength of the incident light 132
is varied from 1546 to 1572 nm. 133

The superprism is a large area defect-free structure. The 134
simulation results show that the feature size of the super- 135
prism is in the range of hundreds of nanometers. It can be 136
fabricated on a large area in one step using soft lithography. 137

FABRICATION 138

Soft lithography is used to fabricate the photonic crystal 139
structures. There are three steps in the soft lithography pro- 140
cedure: (1) master fabrication, (2) PDMS template forma- 141
tion, and (3) pattern transfer. 142

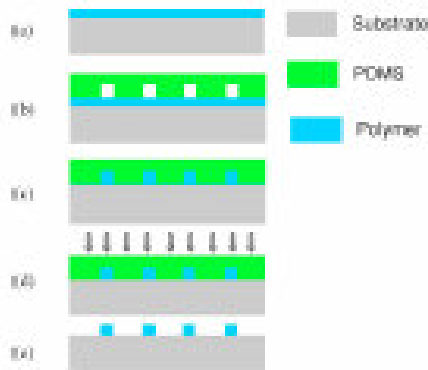


FIG. 3. (Color online) Schematic diagram of the soft lithography process: (a) polymer was dispensed on the substrate; (b) PDMS template was placed on the substrate; (c) filling of the space by capillary; (d) the polymer was cured by UV light; and (e) PDMS template was released.

148 Master fabrication

144 We fabricated the master structures composed of trian-
145 gular arrays of identical holes using a JEOL JBX6000
146 electron-beam lithography (EBL) system. The diameter of
147 the holes ranges from 100 to 500 nm, and the period from
148 200 to 1000 nm. First, a layer of e-beam resist (ER)
149 ZEP520A was coated on a silicon substrate. The patterns
150 were defined by EBL and the exposed ER was developed in
151 the ZED-N50 solution. After developing, it was postbaked
152 on a 100 °C hotplate for 10 min. A 2D triangular array of
153 holes was thus fabricated on the ER.

154 PDMS template formation

155 The PDMS material (Sylgard 184, Dow Corning) is
156 composed of two parts, the base and the curing agent. They
157 were mixed at a ratio of 10:1 in weight and were degassed in
158 vacuum to eliminate air bubbles. Then we poured PDMS
159 prepolymer onto the master and cured it on a hot plate at
160 60 °C for 12 h. The Young's modulus of PDMS is 2 MPa.²²
161 Because the cured PDMS did not adhere to the resist pat-
162 terns, it could be easily peeled off from the master. The 2D
163 photonic crystal structures were transferred from the master
164 to the PDMS template. The holes on the master yield the
165 posts on the PDMS template.

166 Pattern transfer

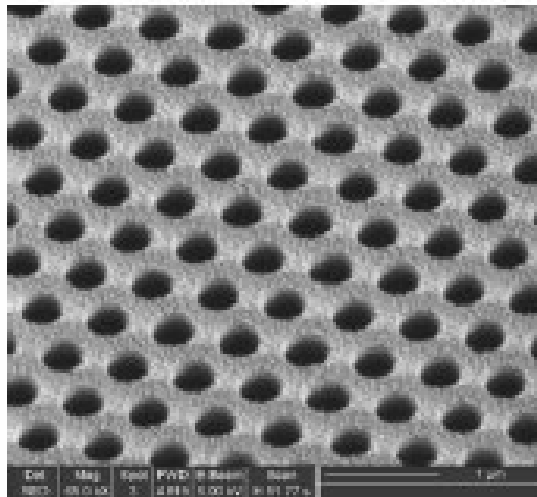
167 The procedures of soft lithography are shown in Fig. 3.
168 A small amount of UV curable acrylate polymer (WIR30-
169 470, ChemOptics, Korea) is dispensed evenly on the sub-
170 strate. The PDMS template is then placed in contact with the
171 substrate without any external force. The capillary force
172 drives the polymer to fill the void spaces of the template,
173 leading to pattern formation. The low viscosity of polymer
174 WIR30-470 (0.2 Pa s) allows the rapid filling of the recessed
175 features of PDMS on the order of microseconds, which were
176 estimated based on the surface tension and viscosity of the
177 polymer.^{23,24} The PDMS template and substrate remain in
178 contact until the polymer fills the void spaces of the tem-
179 plate. Then the prepolymer is cured by exposure to UV ra-
180 diation through the transparent PDMS template. The trans-

mission of a 3-mm-thick PDMS block was measured to be
91% at 365 nm using a Cary 5000 UV-visible-near infrared
(NIR) spectrometer. The PDMS template is subsequently
peeled off, leaving a triangular lattice of holes on the
WIR30-470 polymer. By using the above procedures, the
transfer of photonic crystal patterns is realized. The samples
are postbaked to further remove solvents in the polymer.

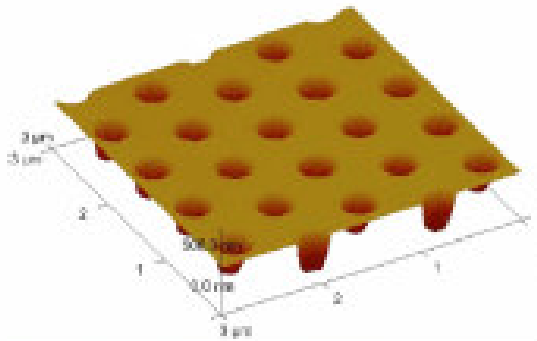
FABRICATION RESULTS AND DISCUSSION

By the above procedures, the 2D photonic crystal struc-
tures were fabricated by soft lithography. The profile of the
molded structures was examined by scanning electron mi-
croscopy (SEM) and atomic force microscopy (AFM). Since
AFM can provide subnanometer vertical resolution, it is sui-
table for the depth and surface roughness measurements of
micro- and nanostructures. Measurements were carried out
with a Digital Instruments AFM Dimension 3100 and the
tapping mode was utilized to avoid surface modification dur-
ing the measurement. The silicon probe (Veeco) with a tip
height of 17.5 μm and cone half angles of 15° side, 15°
front, and 15° back was used in the measurements. 2D tri-
angle photonic crystal structures with air holes of 300 nm in
diameter were shown in Fig. 4(a). The depth of air holes was
375 nm on average measured by AFM shown in Fig. 4(b).
The images clearly demonstrated that an array of air holes of
300 nm diameter with an aspect ratio of 1.25 were replicated
using soft lithography. For reference, we also fabricated ar-
rays of narrow lines, which can be regarded as one-
dimensional (1D) photonic crystals or gratings, by the same
technique. The SEM of the grating structures were shown in
Fig. 5. In Fig. 5(a) the line width, period, and depth are 150,
650, and 122 nm, respectively. In Fig. 5(b) the line width is
200 nm, the period is 400 nm and the depth is 122 nm. It
shows that the resolution of molded structures was down to
150 nm with an aspect ratio of 0.81 using the soft lithogra-
phy technique. During the pattern transfer from a master to a
PDMS template, some problems can arise, such as air
bubbles being trapped in the holes on the master due to the
submicron structures with high pattern density. In previous
work, a reduction of more than 10% in depth from the master
to PDMS template was reported.²⁵ Figure 6 shows the AFM
images and section analysis of the master [in Fig. 6(a)],
PDMS template [in Fig. 6(b)], and molded structures [in Fig.
6(c)]. The depths of holes on each sample were analyzed
along three different crystallographic directions using a soft-
ware (NANOSCOPE III VERSION 6.12R1, Nanoscope, Multi-
mode, DI-Veeco Instruments, Inc.). The three groups of line
profile in the middle column of Fig. 6 show the uniform
depths and periods of the hole/posts patterns along different
crystallographic directions. On average, the depths of master,
PDMS template, and molded structures are 387, 379, and
375 nm, respectively. We also measured the film thickness of
the master structure by using a NANO SPEC microscope.
The thickness of e-beam resist spin coated by 3200 rpm for
1 min on the silicon substrate is 387 nm on average. The film
thickness measurements agree well with AFM measure-
ments. There is a 3% reduction of depth in the molded struc-
tures with respect to the master. There were two steps in-

AG-42



(a)



(b)

FIG. 4. (Color online) (a) SEM micrographs of the 2D molded structure with 309 nm in diameter (lattice constant of 600 nm). (b) AFM images of the 2D molded structure with 375 nm in depth.

involved in the pattern transfer. The depth reductions were 2% from master to PDMS template and 1% from the PDMS template to the molded polymer structures. The reduction is, we believe, primarily attributed to the fact that air is easily trapped in the holes on the master during fabricating the PDMS template. We solved this problem by tilting the master by 5° – 10° with respect to the horizon. Then the PDMS prepolymer was poured on the high level side and it flowed slowly by gravity to the low level side. The experimental results show that the PDMS prepolymer (0.31 Pa s) can better fill in the nanostructures through the current procedure.

Light scattering due to surface roughness is an important

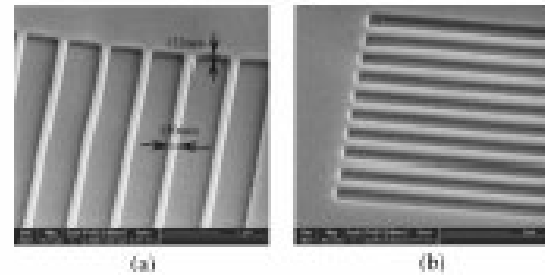


FIG. 5. (Color online) SEM micrographs of the 1D molded structures.

source for optical loss. Sugimoto *et al.* measured the top surface roughness of a waveguide in a GaAs membrane photonic crystal on the order of 1 nm, which gives satisfactorily low optical loss.²⁶ We also analyzed the surface roughness of the molded structures and masters using AFM. Regarding the surface roughness, only a slight increase in the root mean square (rms) roughness (~ 1.2 nm) over $1 \mu\text{m}^2$ area was observed on the molded structures with respect to the master (~ 1.0 nm). We used the same PDMS template to replicate a 2D triangular photonic crystal lattice for three times and the surface roughness remained at the same level.

The pattern collapse is a serious problem in submicron structures with high aspect ratios and/or high pattern density, and it is one of the factors which limit the structure dimensions. There are multiple forms of pattern collapse or defects,²³ but the lateral collapse was found to be the dominant form in our fabricated structures according to our observation. When the high aspect ratio structures are molded at high pattern density, the lateral collapse of neighboring posts occurs during the pattern transfer when the surface tension is large enough to make the neighboring posts contact. Once they contact each other, they adhere together permanently.²⁷ For the high pattern density or high aspect ratio, the posts become more susceptible to the surface tension. If any external force makes the posts bend and they are not vertical to the substrate, the posts are easily in contact with the neighboring posts on the top because of the small spacing between the posts.²⁸ The pattern density and aspect ratio of patterns therefore play an important role in the lateral collapse of PDMS templates. The condition for lateral collapse of post structures was established by Glassmaker *et al.* in 2004.²⁸ To be specific, the critical aspect ratio at which the collapse occurs in PDMS is given by

$$\left(\frac{h}{2a}\right)_c = \frac{1}{2} \left[\frac{27\pi^4 w^6}{32(1-\nu^2)a^2} \left(\frac{E}{\gamma_s}\right)^4 \right]^{1/12} \\ = \frac{1}{2} \left[\frac{27\pi^4 a^4}{32(1-\nu^2)} \left(\frac{w}{a}\right)^6 \left(\frac{E}{\gamma_s}\right)^4 \right]^{1/12},$$

where E is the Young's modulus, a is the radius of post, $2w$ is the spacing between the posts, ν is the Poisson's ratio of PDMS ($\nu=0.5$), and γ_s is the surface energy. The above equation describes the high density pattern having a small critical aspect ratio. For a given pattern density, the critical aspect ratio of posts becomes small as the radius decreases. The model also predicts that the stiff material (high Young's modulus) will increase the stability of posts.

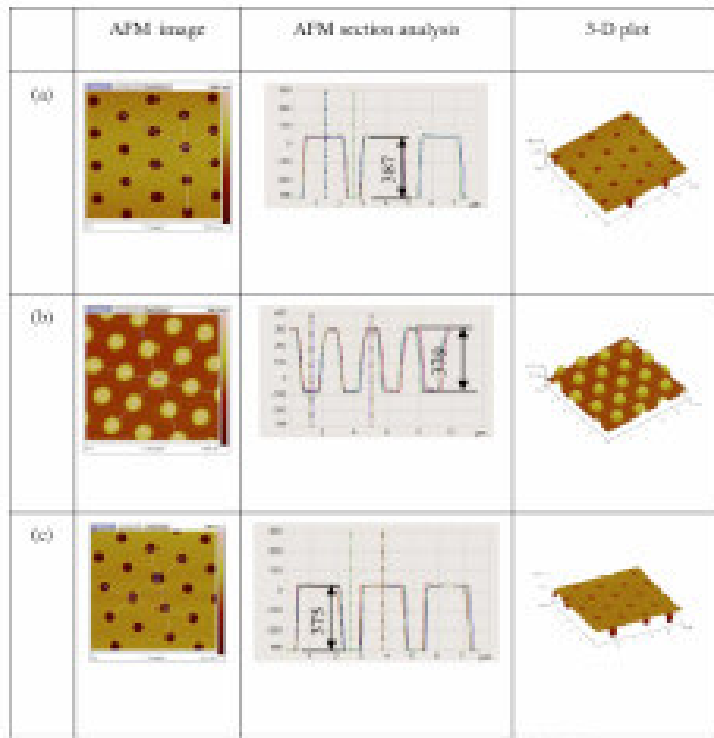


FIG. 6. (Color online) AFM images of the master, PDMS, and molded structures.

From the above equation, we can obtain the critical height (the highest height at which the patterns do not lapse),

$$h_c = \left[\frac{27\pi^4}{32(1-\nu^2)} \left(\frac{w}{a} \right)^6 \left(\frac{E}{\gamma_r} \right)^4 \right]^{1/12} a^{4/3}.$$

For a given pattern density $w/a=1$, we plot the above equation in Fig. 7. The surface energy of PDMS is 55 mJ/cm^2 measured by Chaudhury *et al.* using the JKR technique²⁰ and the Young's modulus of PDMS is 2 MPa .²¹ The area above the line corresponds to the parameter ranges for the stable patterns and the area below the line the collapsed patterns. The 2D triangular photonic crystal lattices

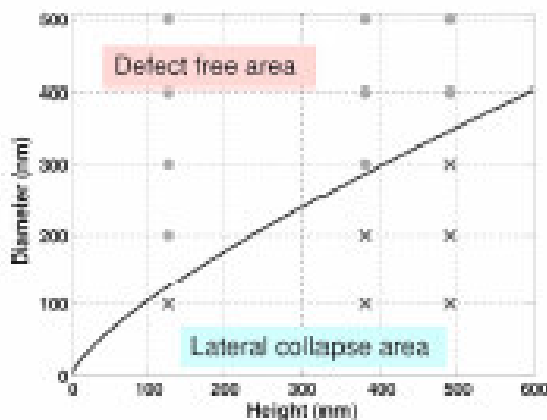


FIG. 7. (Color online) Analysis of the pattern collapse issue. The green dots represent replicated structures, whereas red crosses represent collapsed structures. The curve separating the defect-free and collapsed structures is calculated according to Ref. 28.

with different dimensions and different critical heights obtained in our experiments are also marked in Fig. 7. The dots represent those molded structures without defects; whereas the crosses represent those collapsed structures. The experimental data are in agreement with the values calculated by the above model. The critical height of 200 nm diameter holes is 122 nm . When the dimension of holes increases to 300 nm diameter, the critical height becomes 375 nm . The aspect ratio of these holes is 1.25 . The critical height of 400 nm diameter holes is 490 nm . The above depths are measured by AFM.

To avoid the collapse of PDMS templates, we can increase the Young's modulus of PDMS or use a low surface energy polymer. The Young's modulus of PDMS depends on curing time and mix ratio (base versus curing agent).³⁰ With curing time increasing or mix ratio decreasing, the Young's modulus will increase.

EXPERIMENTAL RESULTS

Optical measurement of the 2D photonic crystal structure with 325 nm diameter and 650 nm period was conducted using a Newport Automatic Alignment station where alignment accuracy down to 100 nm can be precisely controlled. A lensed optical fiber was used to couple a Santes tunable laser light into a fabricated sample. The input lensed fiber is aligned for the TE mode with the electric field vector primarily in plane. The TE polarized light is used for all the measurements presented here. An infrared camera was used to image the light path in photonic crystal superprism from the top surface of the sample. As the wavelength is tuned from 1545 to 1572 nm , the corresponding beam inside the 2D photonic crystal continuously changed propagating direc-

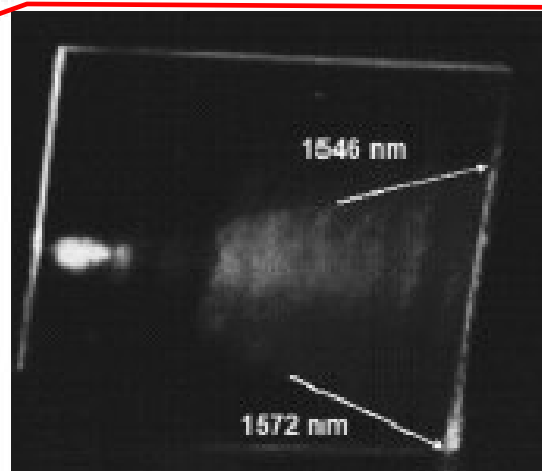


FIG. 8. (Color online) Microscope images for beam steering by wavelength: (1) beam angle at 1546 nm and (2) beam angle at 1572 nm.

tion from -19° to 20° . The beam propagation angles were shown in Fig. 8 for the beam wavelength tuning from 1546 and 1572 nm. The beam propagation direction was changed from negative to positive refraction angles with increasing wavelength. This is consistent with the numerical simulation results. The physical mechanism behind this effect can be explained with the dispersion surface. It means the shape of the dispersion surface experiences a large change with the wavelength increasing from 1546 to 1572 nm.

There is still some deviation between the experimental data and numerical simulation results. This can be caused by the imperfection of the fabricated samples. The incident light was offset from designed angle 36.9° to smaller incident angle. From the simulation results, the light propagation angle in the photonic crystal changes when the incident angle is 36.5° instead of 36.9° , while the simulation results show the propagation angle in photonic crystals changes from -26° to 27° . Reasonable agreement is obtained between the simulation results and experimental data.

CONCLUSION

We have fabricated the 2D photonic crystal superprism structures by soft lithography and demonstrated the superprism effect in 2D photonic crystal structure at near-infrared wavelength. The beam propagation angle changed 39° when the input wavelength was varied from 1546 to 1572 nm. An aspect ratio of 1.25 is achieved for a photonic crystal with 300 nm air holes. The depth of the master and that of molded patterns have only 3% difference. The soft lithography with PDMS templates represents a simple, low cost, and reliable approach for fabrication of fine features as small as 150 nm in linewidth without distortions or defects over a large patterned area.

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